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#### 100V N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on) max</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
100V	220mΩ @ V <sub>GS</sub> = 10V	1.6A
	250mΩ @ V <sub>GS</sub> = 4.5V	1.3A

# **Description**

This new generation MOSFET has been designed to minimize the onstate resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

Load Switch

### **Features and Benefits**

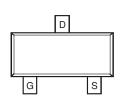
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

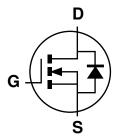
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe.
   Solderable per MIL-STD-202, Method 208 3
- Weight: 0.0072 grams (approximate)







Pin Configuration



Equivalent Circuit

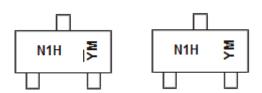
#### **Ordering Information** (Note 4)

Part Number	Compliance	Case	Packaging
DMN10H220L-7	Standard	SOT23	3,000/Tape & Reel
DMN10H220L-13	Standard	SOT23	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



N1H = Marking Code

 $\underline{YM}$  = Date Code Marking for SAT (Shanghai Assembly/ Test site)  $\underline{YM}$  = Date Code Marking for CAT (Chengdu Assembly/ Test site)  $\underline{Y}$  or  $\underline{Y}$  = Year (ex: A = 2013)

M = Month (ex: 9 = September)

Date Code Key

Date Code Rey												
Year	201	3	2014		2015	20	16	2017		2018	2	2019
Code	Α		В		С		)	Е		F		G
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		$V_{DSS}$	100	V	
Gate-Source Voltage		$V_{GSS}$	±16	V	
		$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	1.6 1.3	Α
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	(Note 5)	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	1.4 1.1	Α
Maximum Continuous Body Diode Forward Curren	t (Note 6)	I <sub>S</sub>	0.6	Α	
Pulsed Drain Current (10µs pulse, duty cycle = 1%	)	I <sub>DM</sub>	8	Α	

# **Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Total Power Dissipation (Note 6)	$T_A = +25$ °C	J	1.3	W	
Total Power Dissipation (Note 6)	T <sub>A</sub> = +70°C	$P_{D}$	0.8		
Thermal Resistance, Junction to Ambient	(Note 6)	ם	94	°C/W	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	177	C/VV	
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C	

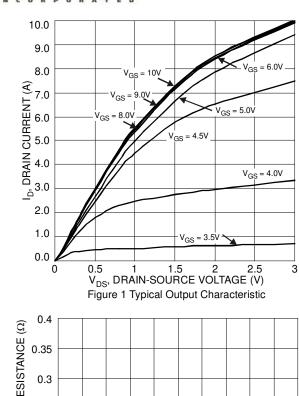
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

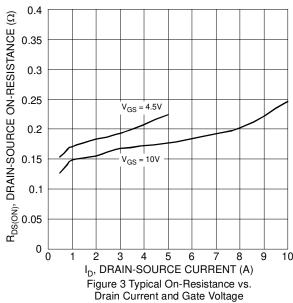
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	$BV_{DSS}$	100	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 100V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	1		2.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	В		_	220	mΩ	$V_{GS} = 10V, I_D = 1.6A$	
Static Drain-Source On-nesistance	R <sub>DS (ON)</sub>	_	_	250	11177	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 1.3A	
Diode Forward Voltage	$V_{SD}$	_	0.7	1.2	V	$V_{GS} = 0V, I_S = 1.1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	401	_		$V_{DS} = 25V$ , $V_{GS} = 0V$ f = 1MHz	
Output Capacitance	Coss	_	22	_	рF		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	17	_			
Gate Resistnace	$R_g$	_	2.1	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	$Q_g$	_	4.1	_		V 50V L 4.04	
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	8.3	_	nC		
Gate-Source Charge	Q <sub>gs</sub>	_	1.5	_	no no	$V_{DS} = 50V, I_D = 1.6A$	
Gate-Drain Charge	$Q_{gd}$	_	2	_			
Turn-On Delay Time	t <sub>D(on)</sub>	_	6.8	_			
Turn-On Rise Time	t <sub>r</sub>	_	8.2	_	200	$V_{DS} = 50V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	t <sub>D(off)</sub>	_	7.9	_	ns	$R_G = 6.8\Omega, I_D = 1A$	
Turn-Off Fall Time	t <sub>f</sub>	_	3.6	_			
Reverse Recovery Time	t <sub>rr</sub>	_	17	_	ns	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	
Reverse Recovery Charge	Q <sub>rr</sub>	_	9.8	_	nC	I <sub>F</sub> = 1.1A, di/dt =100A/μs	

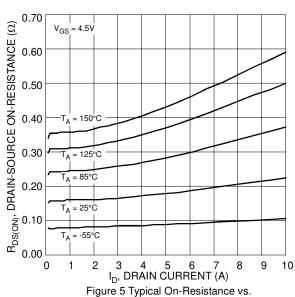
Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
  7 .Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.

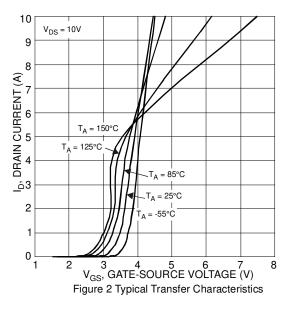


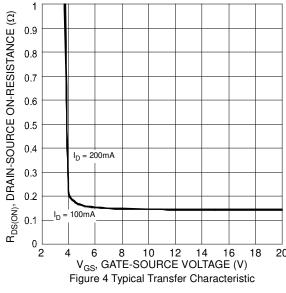






Drain Current and Temperature





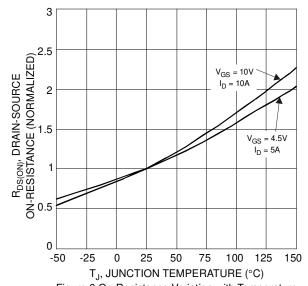
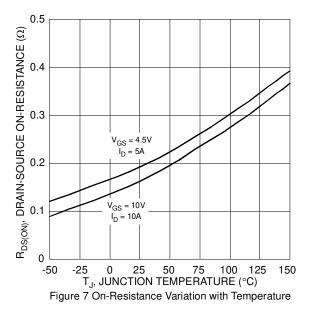
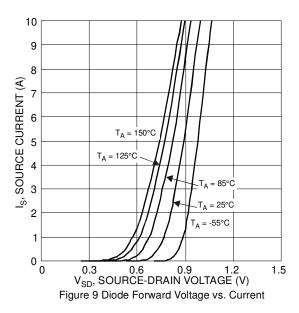
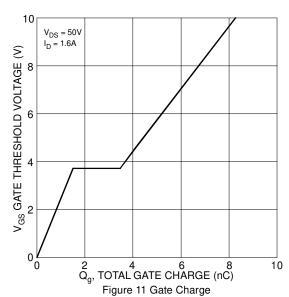


Figure 6 On-Resistance Variation with Temperature









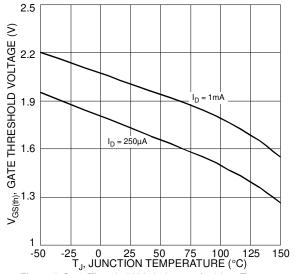
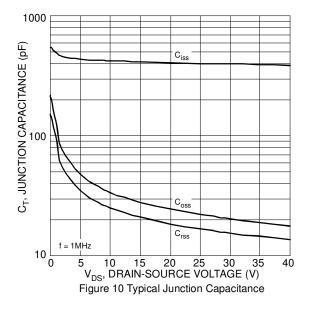
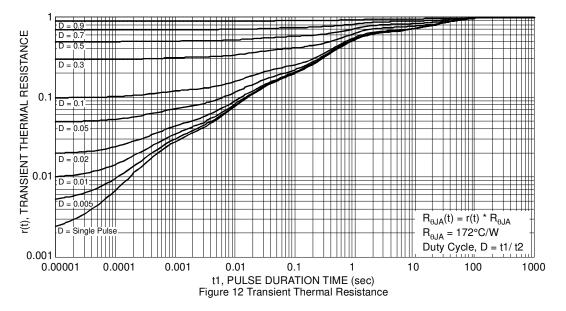


Figure 8 Gate Threshold Variation vs. Ambient Temperature

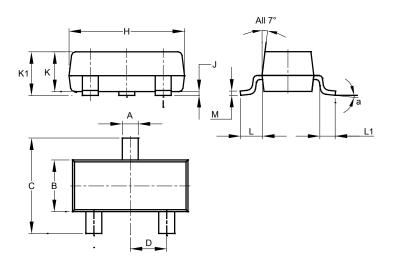






## **Package Outline Dimensions**

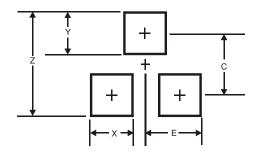
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
<b>a</b> 8°								
All	All Dimensions in mm							

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Υ	0.9
С	2.0
E	1.35



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